

**Amendments to the Claims:**

Please cancel claims 1-14 and 48 as set forth below.

1.-14. (Cancelled)

15-27. (Canceled)

28. (Previously Presented) A packaged microelectronic device comprising:  
a die having a first side and a second side opposite to the first side, the die further having  
an integrated circuit positioned between the first and second sides;  
a bond-pad positioned on the first side of the die and electrically coupled to the integrated  
circuit;  
a passage extending completely through the die and aligned with and extending through  
the bond-pad;  
a first conductive material deposited in a first portion of the passage adjacent to the first  
side of the die to form a conductive plug electrically connected to the bond-pad;  
and  
a second conductive material deposited in a second portion of the passage in contact with  
the conductive plug to at least generally fill the passage from the conductive plug  
to the second side of the die.

29. (Original) The packaged microelectronic device of claim 28, further comprising  
an insulative layer deposited in the passage between the die and the first and second conductive  
materials.

30. (Previously Presented) The packaged microelectronic device of claim 28, further  
comprising an insulative layer deposited in the passage between the die and the first and second  
conductive materials.

31. (Original) The packaged microelectronic device of claim 28 wherein the first  
conductive material includes an electronic ink in contact with an exposed surface of the bond-  
pad.

32. (Original) The packaged microelectronic device of claim 28 wherein the first conductive material includes a nano-particle deposition in contact with an exposed surface of the bond-pad.

33. (Previously Presented) A microfeature workpiece having a first side and a second side opposite to the first side, the microfeature workpiece comprising:

at least one die;

a bond-pad formed on the first side of the microfeature workpiece;

a passage extending completely through the bond-pad and the die from the first side of the microfeature workpiece to the second side of the microfeature workpiece;

a first conductive material deposited in a first portion of the passage adjacent to the first side of the microfeature workpiece to form a conductive plug in contact with the bond-pad; and

a second conductive material deposited in a second portion of the passage in contact with the conductive plug to at least generally fill the passage from the conductive plug to the second side of the microfeature workpiece.

34. (Original) The microfeature workpiece of claim 33 wherein the first conductive material includes an electronic ink.

35. (Original) The microfeature workpiece of claim 33 wherein the first conductive material includes a nano-particle deposition.

36. (Previously Presented) The microfeature workpiece of claim 33, further comprising an insulative layer deposited in the passage between the die and the first and second conductive materials.

37. (Original) The microfeature workpiece of claim 33, further comprising a metallic layer formed on the first side of the microfeature workpiece.

38. (Canceled)

39. (Original) A microelectronic device set comprising:  
a first microelectronic device having:  
a first die with a first integrated circuit and a first bond-pad electrically coupled to the first integrated circuit, the first die further including a passage extending completely through the first die and the first bond-pad; and  
a conductive interconnect deposited in the passage, the conductive interconnect including a first conductive material deposited in a first portion of the passage to form a conductive plug, and a second conductive material deposited in a second portion of the passage in contact with the conductive plug to at least generally fill the passage; and  
at least a second microelectronic device having a second die with a second integrated circuit and a second bond-pad electrically coupled to the second integrated circuit, wherein the second bond-pad is electrically coupled to the conductive interconnect of the first microelectronic device.
40. (Original) The microelectronic device set of claim 39 wherein the first microelectronic device is attached to the second microelectronic device in a stacked-die arrangement.
41. (Original) The microelectronic device set of claim 39, further comprising a solder ball disposed between the conductive interconnect of the first microelectronic device and the second bond-pad of the second microelectronic device to electrically couple the first bond-pad to the second bond-pad.
42. (Original) The microelectronic device set of claim 39 wherein the passage is a first passage, wherein the second microelectronic device further includes a second passage extending through the second die and the second bond-pad, and wherein the second passage is completely filled with a third conductive material.
43. (Original) The microelectronic device set of claim 39 wherein the first microelectronic device further includes a redistribution layer formed on the first die, the

redistribution layer including a conductive line having a first end portion attached to the first bond-pad and a second end portion positioned outward of the first end portion, wherein the second end portion is configured to receive electrical signals and transmit the signals to at least the first integrated circuit of the first die and the second integrated circuit of the second die.

44. (Previously Presented) A microelectronic device set comprising:

a first microelectronic device having:

a first die with a first integrated circuit and a first bond-pad electrically coupled to the first integrated circuit, the first die further including a passage aligned with and extending through the first bond-pad; and

a conductive interconnect deposited in the passage, the conductive interconnect including a first conductive material deposited in a first portion of the passage to form a conductive plug in contact with the bond-pad, and a second conductive material deposited in a second portion of the passage in contact with the conductive plug to at least generally fill the passage; and

at least a second microelectronic device having a second die with a second integrated circuit and a second bond-pad electrically coupled to the second integrated circuit, wherein the second bond-pad is electrically coupled to the first bond-pad of the first microelectronic device.

45. (Previously Presented) The packaged microelectronic device of claim 44, further comprising an insulative layer deposited in the passage between the first die and the first and second conductive materials.

46. (Original) The packaged microelectronic device of claim 44 wherein the first conductive material includes an electronic ink in contact with an exposed surface of the bond-pad.

47. (Original) The packaged microelectronic device of claim 44 wherein the first conductive material includes a nano-particle deposition in contact with an exposed surface of the bond-pad.

48. (Cancelled)

49. (Previously Presented) The packaged microelectronic device of claim 28, further comprising an insulative layer deposited in the passage, wherein the second conductive material contacts the conductive plug and the insulative layer.

50. (Previously Presented) The microfeature workpiece of claim 33, further comprising an insulative layer deposited in the passage, wherein the second conductive material contacts the conductive plug and the insulative material.

51. (Previously Presented) The microelectronic device set of claim 39 wherein the first microelectronic device further includes an insulative layer deposited in the passage, and wherein the second conductive material contacts the conductive plug and the insulative layer.

52. (Previously Presented) The microelectronic device set of claim 44 wherein the first microelectronic device further includes an insulative layer deposited in the passage, and wherein the second conductive material contacts the conductive plug and the insulative layer.